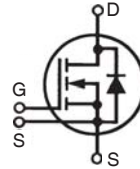
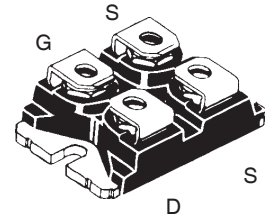


**X3-Class HiPerFET™
Power MOSFET**
IXFN300N20X3

$$V_{DSS} = 200V$$

$$I_{D25} = 300A$$

$$R_{DS(on)} \leq 3.5m\Omega$$

 N-Channel Enhancement Mode
Avalanche Rated

 miniBLOC, SOT-227
 E153432

 G = Gate D = Drain
 S = Source

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	200	V
V_{DGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}, R_{GS} = 1M\Omega$	200	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$ (Chip Capability)	300	A
$I_{L(RMS)}$	External Lead Current Limit	200	A
I_{DM}	$T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM}	700	A
I_A	$T_C = 25^\circ\text{C}$	150	A
E_{AS}	$T_C = 25^\circ\text{C}$	3.5	J
P_D	$T_C = 25^\circ\text{C}$	695	W
dv/dt	$I_S \leq I_{DM}, V_{DD} \leq V_{DSS}, T_J \leq 150^\circ\text{C}$	20	V/ns
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS $t = 1$ minute	2500	V~
	$I_{ISOL} \leq 1\text{mA}$ $t = 1$ second	3000	V~
M_d	Mounting Torque	1.5/13	Nm/lb.in
	Terminal Connection Torque	1.3/11.5	Nm/lb.in
Weight		30	g

Features

- International Standard Package
- miniBLOC, with Aluminium Nitride Isolation
- Isolation Voltage 2500V~
- High Current Handling Capability
- Avalanche Rated
- Low $R_{DS(on)}$

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V, I_D = 3\text{mA}$	200		V
$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 8\text{mA}$	2.5		V
I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 200 nA
I_{DSS}	$V_{DS} = V_{DSS}, V_{GS} = 0V$ $T_J = 125^\circ\text{C}$			25 μA 1.5 mA
$R_{DS(on)}$	$V_{GS} = 10V, I_D = 150A$, Note 1			3.5 m Ω

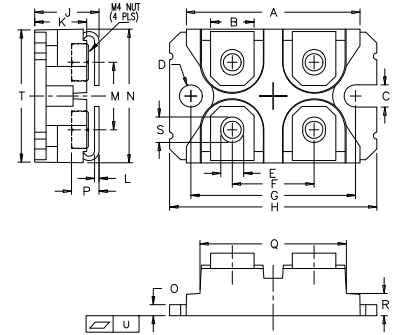
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
g_{fs}	$V_{DS} = 10\text{V}$, $I_D = 60\text{A}$, Note 1	80	135	S
R_{Gi}	Gate Input Resistance		1.8	Ω
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		23.8	nF
C_{oss}			4.0	nF
C_{rss}			3.2	pF
Effective Output Capacitance				
$C_{o(er)}$	Energy related	$V_{GS} = 0\text{V}$ $V_{DS} = 0.8 \cdot V_{DSS}$	1640	pF
$C_{o(tr)}$	Time related		5640	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 150\text{A}$ $R_G = 1\Omega$ (External)		44	ns
t_r			43	ns
$t_{d(off)}$			184	ns
t_f			13	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 150\text{A}$		375	nC
Q_{gs}			117	nC
Q_{gd}			94	nC
R_{thJC}				0.18°C/W
R_{thCS}		0.05		$^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
I_S	$V_{GS} = 0\text{V}$			300 A
I_{SM}	Repetitive, pulse Width Limited by T_{JM}			1200 A
V_{SD}	$I_F = 100\text{A}$, $V_{GS} = 0\text{V}$, Note 1			1.4 V
t_{rr}	$I_F = 150\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$		172	ns
Q_{RM}			1.1	μC
I_{RM}			12.8	A

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

SOT-227B (IXFN) Outline



(M4 screws (4x) supplied)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

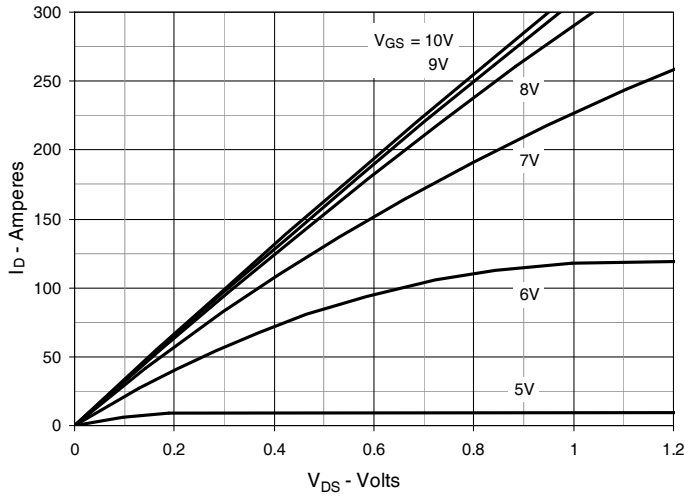


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

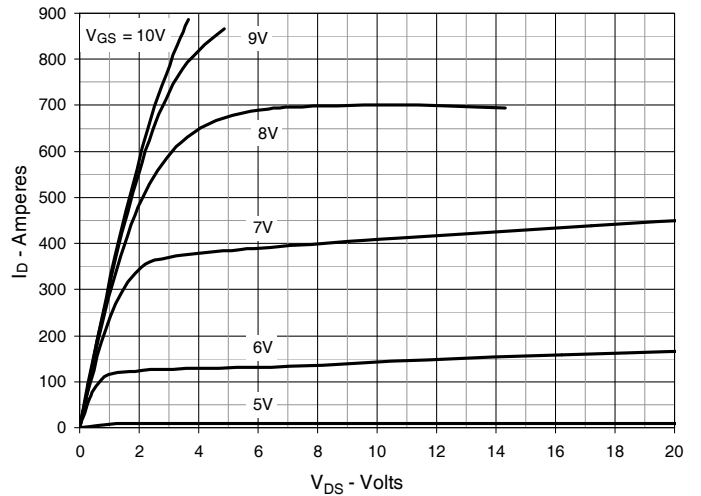


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

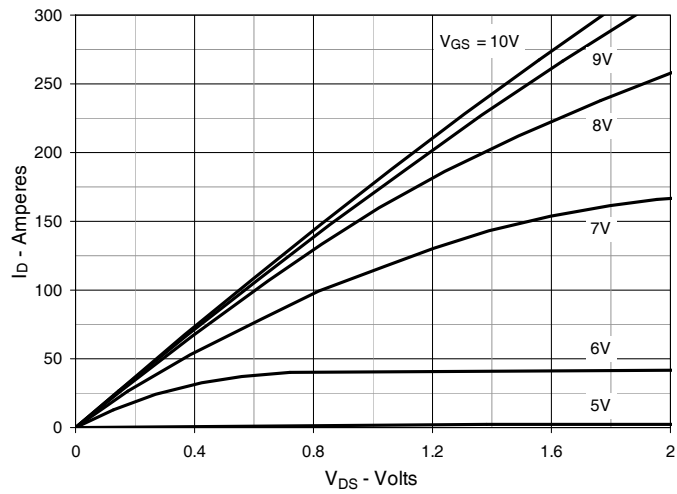


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 150\text{A}$ Value vs. Junction Temperature

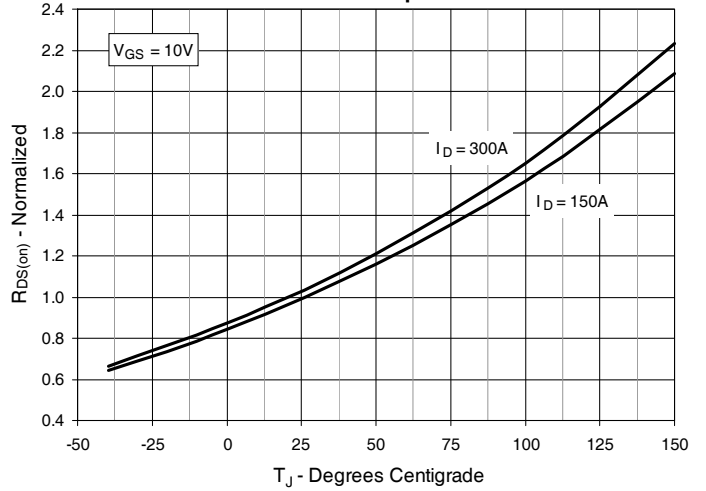


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 150\text{A}$ Value vs. Drain Current

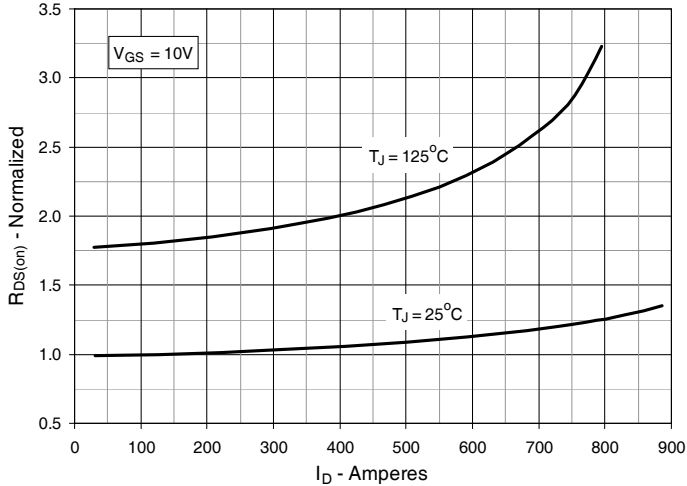


Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature

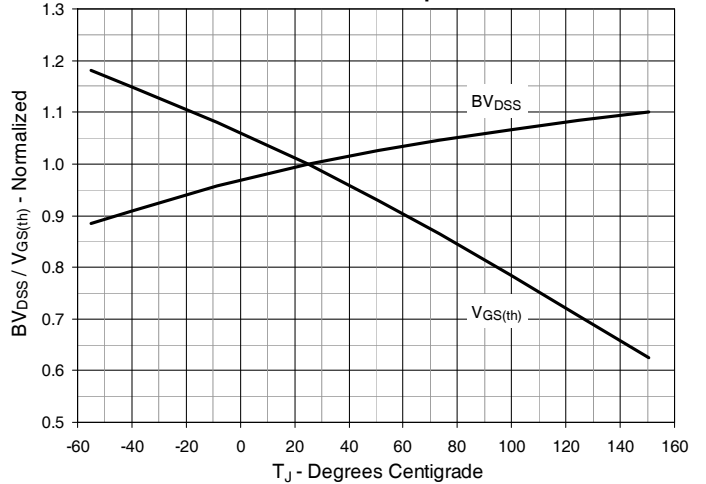


Fig. 7. Maximum Drain Current vs. Case Temperature

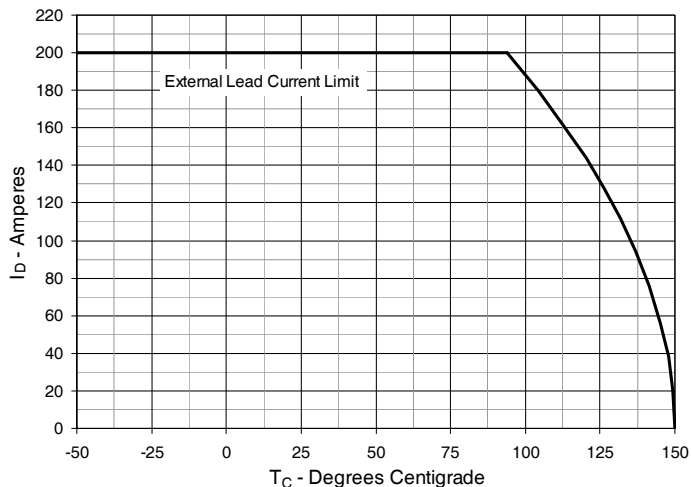


Fig. 8. Input Admittance

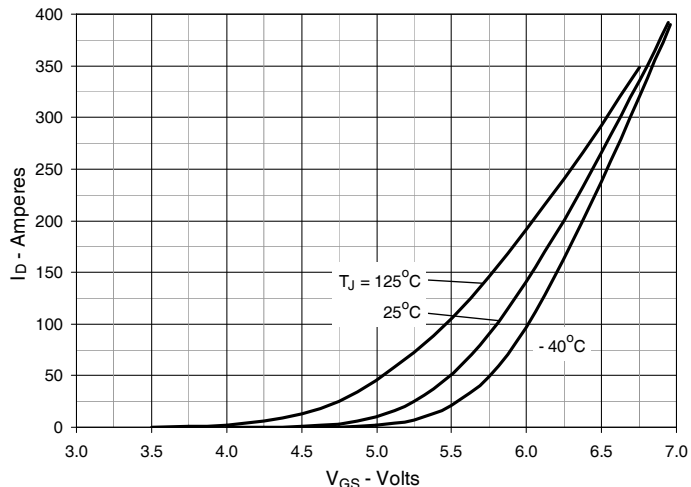


Fig. 9. Transconductance

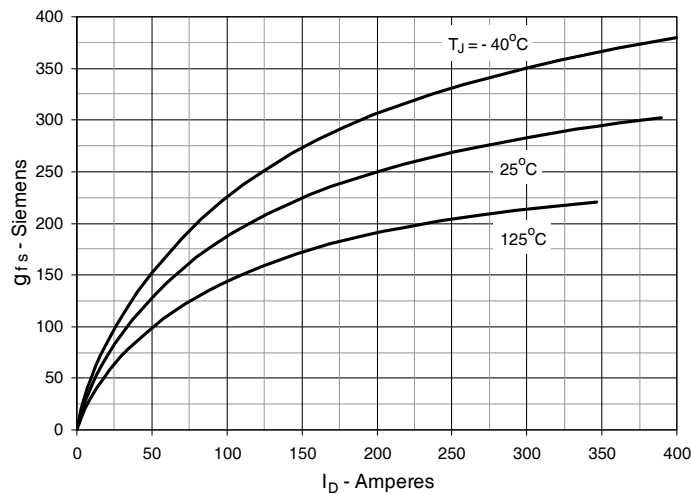


Fig. 10. Forward Voltage Drop of Intrinsic Diode

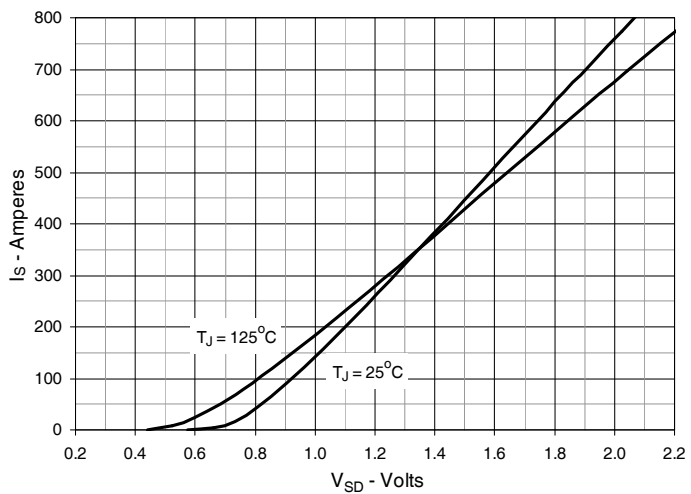


Fig. 11. Gate Charge

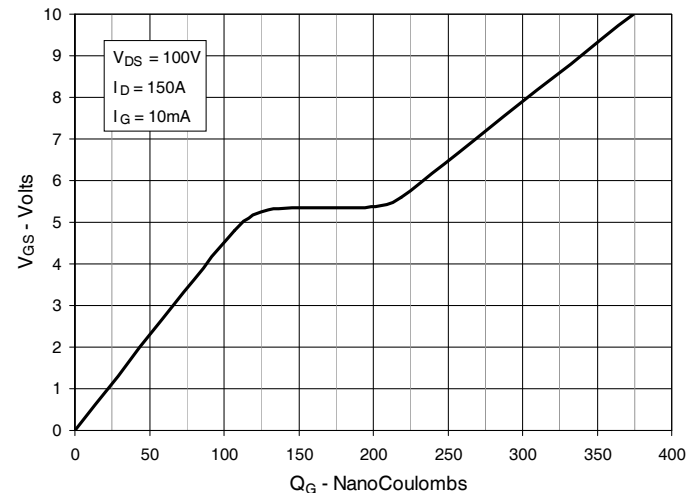


Fig. 12. Capacitance

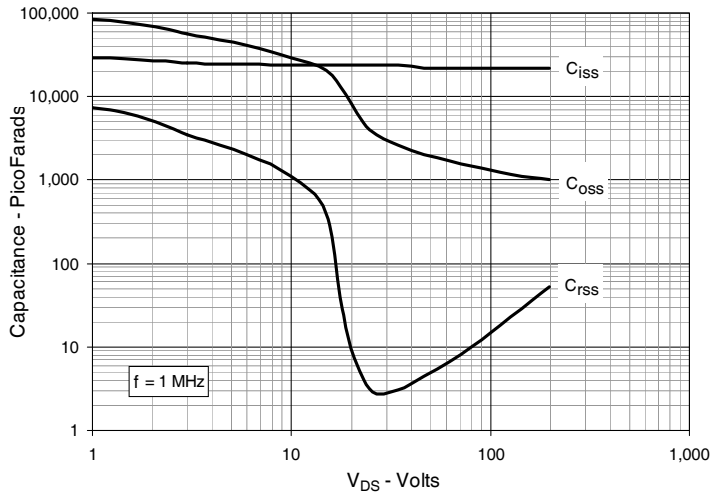
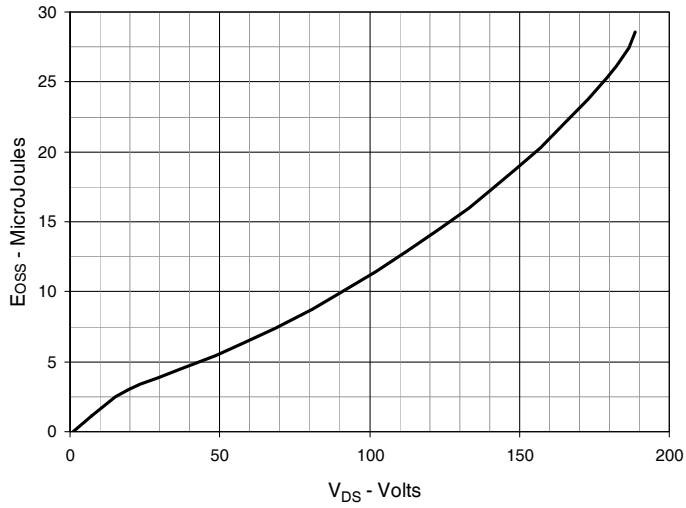
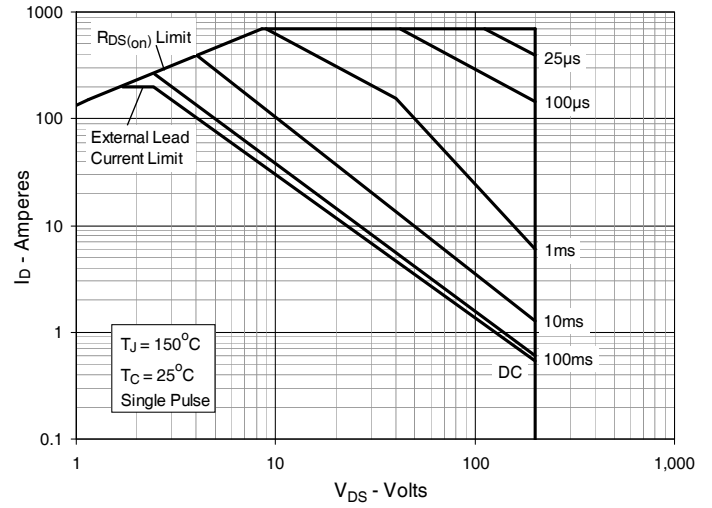
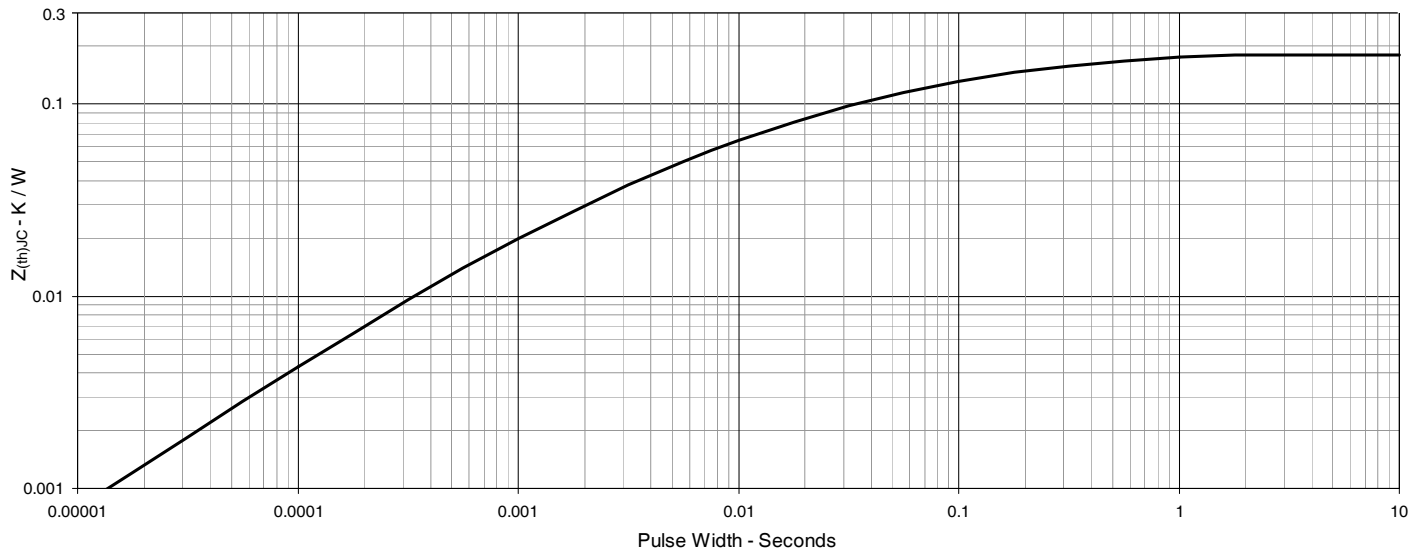


Fig. 13. Output Capacitance Stored Energy

Fig. 14. Forward-Bias Safe Operating Area

Fig. 15. Maximum Transient Thermal Impedance


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